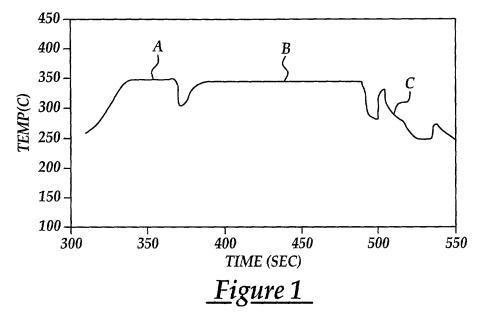
Inventor(s): Wang, et al Serial No.: To Be Assigned Filed: Herewith

Method For Depositing Silicon Oxide Incorporating An Outgassing Step

Attorney Docket No.: 67,200-318



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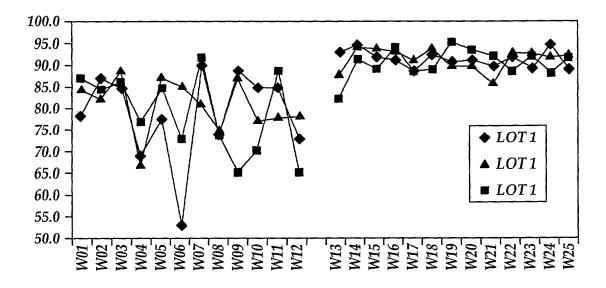
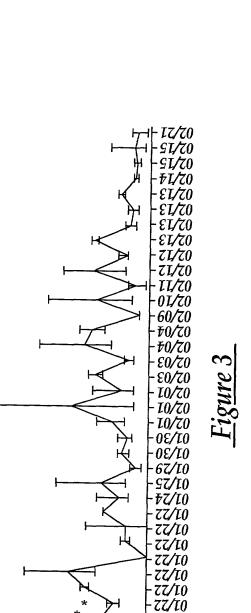


Figure 2

Inventor(s): Wang, et al Serial No.: To Be Assigned Filed: Herewith

Method For Depositing Silicon Oxide Incorporating An Outgassing Step Attorney Docket No.: 67,200-318 For:



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	LOT3	HEAT IID GO CEC	HEAT UP 60 SEC		00.10			94.50		86.39	
	01	STD (5 SEC)	(0000) 000	81.39		6.33		89.01		67.28	
	LOT 2	HEAT UP 60 SEC		90.64		3.33		95.29		82.72	
	OT	STD (5 SEC)		79.30		9.28		91.88		65.45	
	LOT1	HEAT UP 60 SEC STD (5 SEC) HEAT UP 60 SEC STD (5 SEC)		91.68		1.92		95.03		10.68	
		STD (5 SEC)	3	/9.08		10.46		90.31	٠, ٠, ٠, ٠, ٠, ٠, ٠, ٠, ٠, ٠, ٠, ٠, ٠, ٠	53.40	
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